In the Claims:

Please cancel claims 1-15 The claims are as follows.

1-15. (Canceled)

16. (Original) A bipolar transistor, comprising:

a base;

an emitter contact formed within the base;

a base contact formed within the base; and

a first wiring stack formed atop the emitter contact and a second wiring stack formed atop the base contact, wherein the second wiring stack includes at least one more wiring level than the first wiring stack.

17. (Original) The bipolar transistor of claim 16, further comprising a collector contact formed within a subcollector.

18. (Original) The bipolar transistor of claim 16, wherein the emitter contact surrounds the base contact on at least two sides.

19. (Original) The bipolar transistor of claim 16, wherein the emitter contact forms a ring around the base contact.

20. (Original) The bipolar transistor of claim 16, wherein the base contact is a point contact.

21. (Original) A device, comprising:

at least two bipolar transistors, wherein each bipolar transistor further comprises:

a base contact;

an emitter contact surrounding the base contact; and

wherein at least one side of the emitter contact of the at least two bipolar transistors are in electrical contact.

22. (Original) The device of claim 21, wherein the emitter contact forms a ring around the base contact.

23. (Original) The device of claim 21, wherein the base contact is a point contact.

24. (Original) The device of claim 21, wherein wires of the base contact and wires of the emitter contact are vertically stacked atop the contacts.

25. (Original) The device of claim 24, wherein the wires of the base contact are stacked at a level higher than the wires of the emitter contact.

26. (Original) The device of claim 21, further including a collector contact.

27. (Original) The device of claim 26, wherein wires of the collector contact are stacked higher than wires of the emitter contact.

28. (Original) The device of claim 21, wherein at least one side of each emitter contact of the electrically connected transistors is in physical contact.

29. (Original) A device, comprising:

at least two bipolar transistors, wherein the bipolar transistors are electrically connected to one another, wherein a first bipolar transistor has a first wiring stack and a second bipolar transistor has a second wiring stack, and wherein the second wiring stack comprises at least one more wiring level than the first wiring stack.

30. (Original) The device of claim 29, wherein the bipolar transistors comprise:

a base contact; and

an emitter contact surrounding the base contact.

31. (Original) The device of claim 29, wherein current is supplied to the first bipolar transistor.